



**BA217/BA218** T-01-09  
General Purpose Diodes

- WIV... 10 V to 100 V
- $t_{rr}$ ... 4ns (MAX) BA216-218

PACKAGES	
BA217	DO-35
BA218	DO-35

**ABSOLUTE MAXIMUM RATINGS (Note 1)**

**Temperatures**

Storage Temperature Range	-65°C to +200°C
Maximum Junction Operating Temperature	+175°C
Lead Temperature	+260°C

**Power Dissipation (Note 2)**

Maximum Total Power Dissipation at 25°C Ambient	500 mW
Linear Power Derating Factor (from 25°C)	3.33 mW/°C

**Maximum Voltage and Currents**

WIV	Working Inverse Voltage	BA218	50 V	BA217	30 V
$I_F$	Continuous Forward Current				100 mA
$I_f$	Peak Repetitive Forward Current				300 mA
$I_f(\text{surge})$	Peak Forward Surge Current				400 mA
	Pulse Width = 1 s				1.0 A
	Pulse Width = 1 $\mu$ s				4.0 A

**ELECTRICAL CHARACTERISTICS (25°C Ambient Temperature unless otherwise noted)**

SYMBOL	CHARACTERISTIC	BA217 • BA218		UNITS	TEST CONDITIONS
		MIN	MAX		
$V_F$	Forward Voltage		1.50		$I_F = 100 \text{ mA}$ $I_F = 50 \text{ mA}$ $I_F = 15 \text{ mA}$ $I_F = 10 \text{ mA}$ $I_F = 3.0 \text{ mA}$ $I_F = 1.0 \text{ mA}$ $I_F = 0.2 \text{ mA}$
			1.00		
			0.70		
$I_R$	Reverse Current		50	nA	$V_R = 10 \text{ V}$
		BA217	50	nA	$V_R = 10 \text{ V}$
		BA218	200	nA	$V_R = 25 \text{ V}$
		BA217	200	nA	$V_R = 30 \text{ V}$
		BA218		nA	$V_R = 50 \text{ V}$
				nA	$V_R = 50 \text{ V}$
				nA	$V_R = 100 \text{ V}$
C	Capacitance		3.0	pF	$V_R = 0, f = 1 \text{ MHz}$
$t_{rr}$	Reverse Recovery Time		4.0	ns	$I_F = 10 \text{ mA}, I_R = 60 \text{ mA}$ $R_L = 100 \Omega$ (Note 3)
				ns	$I_F = 30 \text{ mA}, I_R = 30 \text{ mA}$ $R_L = 100 \Omega$ (Note 4)

**NOTES:**

1. These ratings are limiting values above which the serviceability of the diode may be impaired.
2. These are steady state limits. The factory should be consulted on applications involving pulsed or low duty-cycle operation.
3. Recovery to  $I_R = 1 \text{ mA}$ .
4. Recovery to  $I_R = 3 \text{ mA}$ .
5. For product family characteristic curves, refer to Chapter 4, D4